



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



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Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- $BV_{CEO} > 400V$
- $I_C = 225mA$ Continuous Collector Current
- $I_{CM} = 500mA$ Peak Pulse Current
- Excellent h_{FE} Characteristics up to 100mA
- Low saturation voltage $V_{CE(sat)} < 200mV @ 20mA$
- Complementary PNP Type: NK-FCX558Q

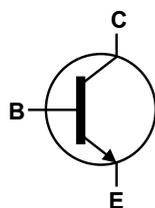
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.055 grams (Approximate)

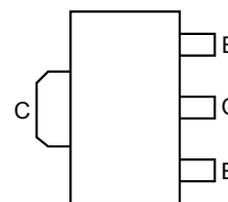
SOT89



Top View



Equivalent Circuit



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	225	mA
Peak Pulse Current	I_{CM}	500	mA
Base Current	I_B	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

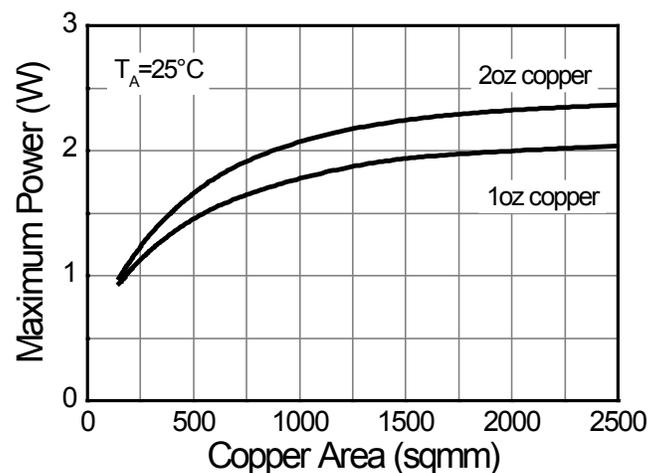
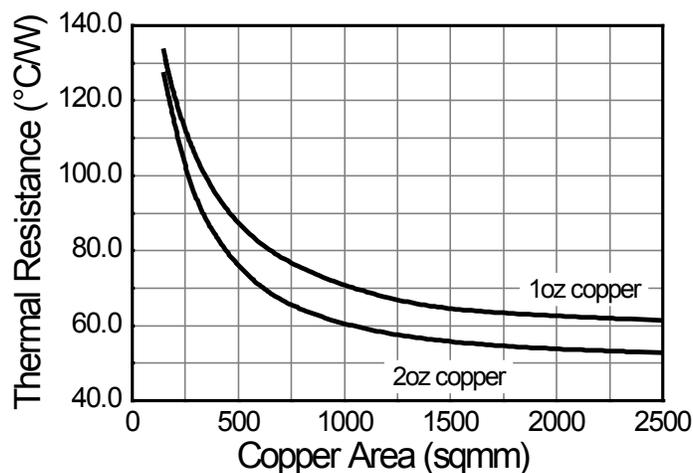
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	0.7	W
		1	
		1.5	
		2	
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	178	$^\circ\text{C/W}$
		125	
		83	
		60	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	22	$^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 10)

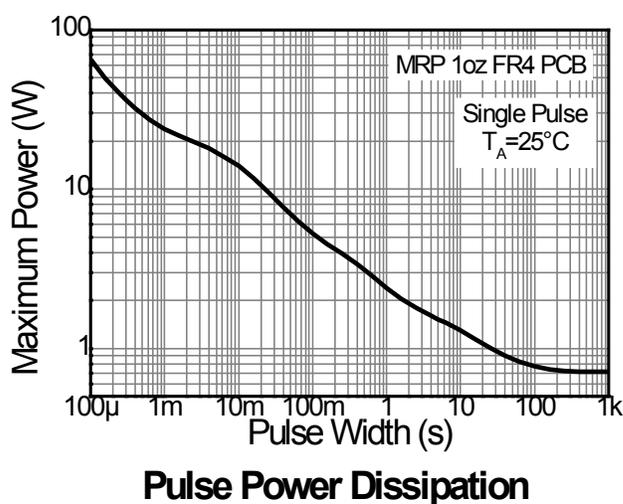
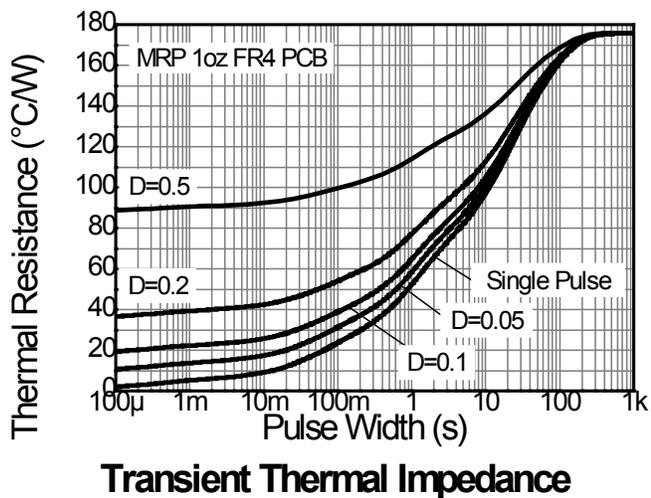
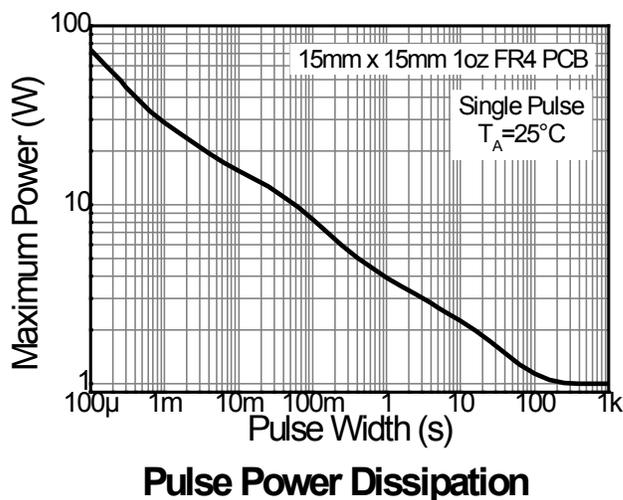
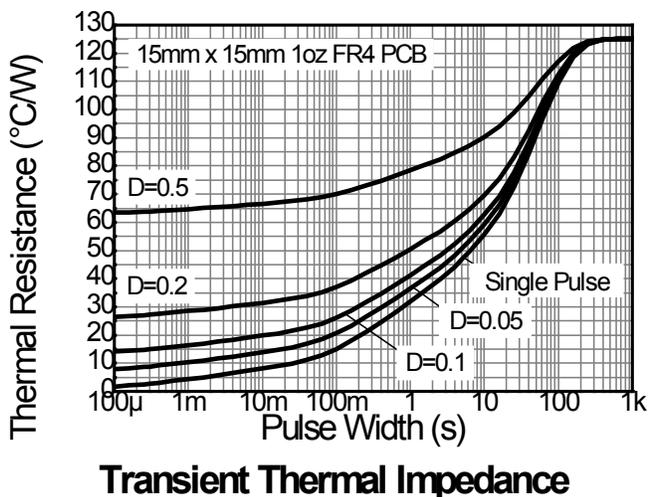
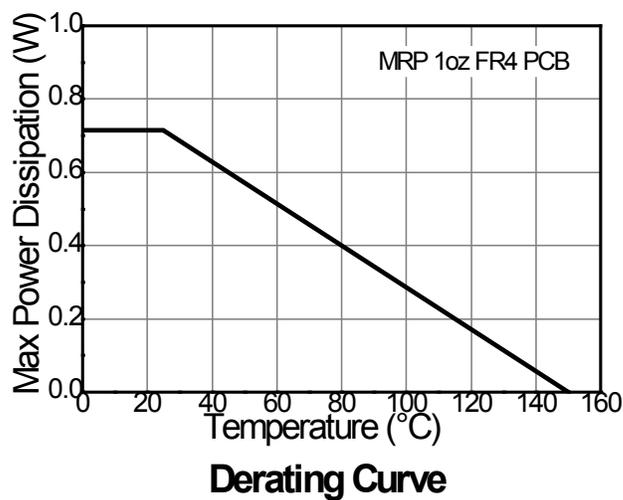
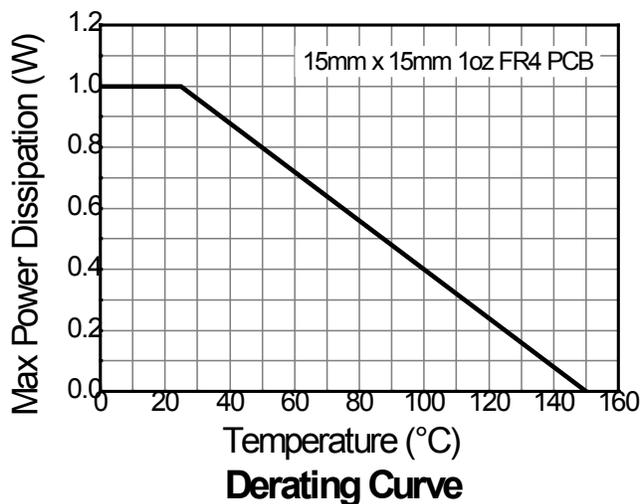
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.
 - Same as Note 5, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted with the exposed collector pad on 50mm x 50mm 1oz copper.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



Thermal Characteristics and Derating Information (cont.)

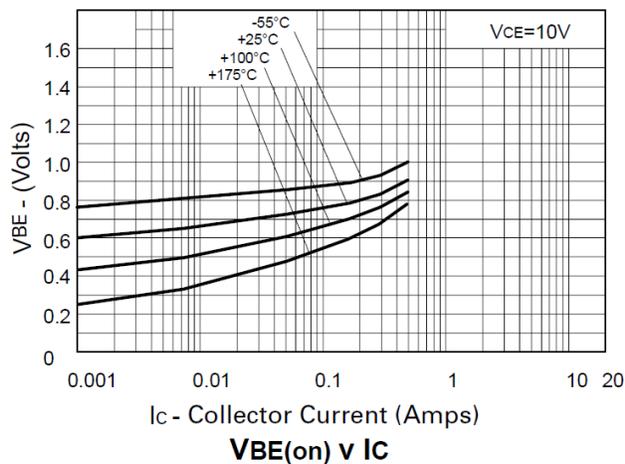
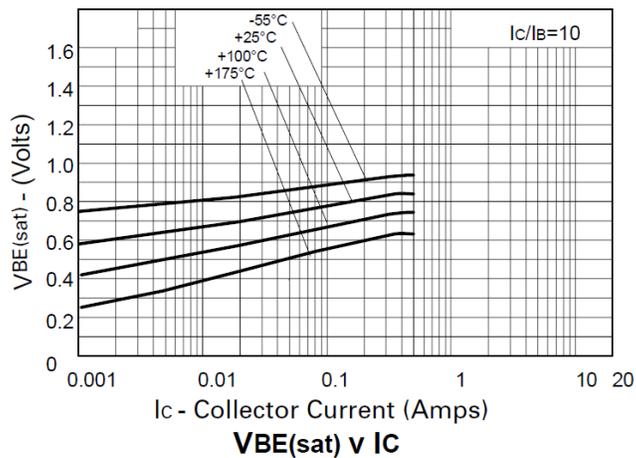
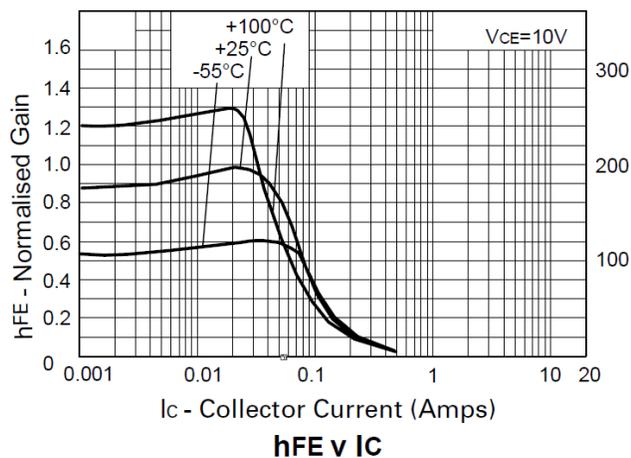
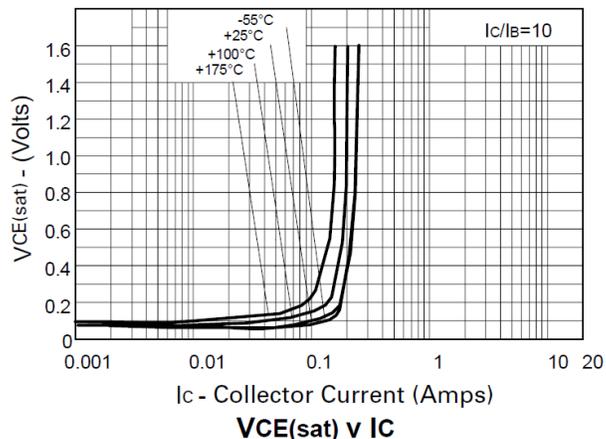
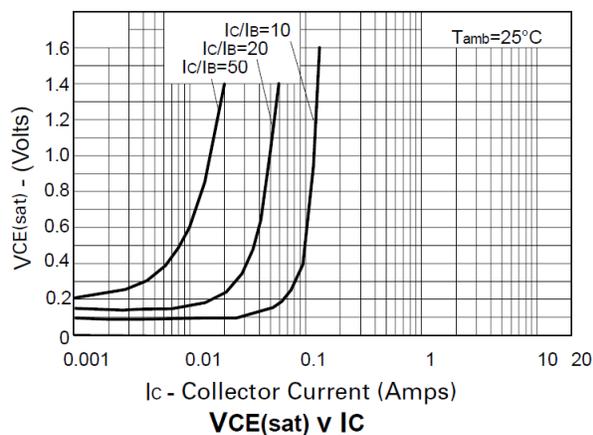


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

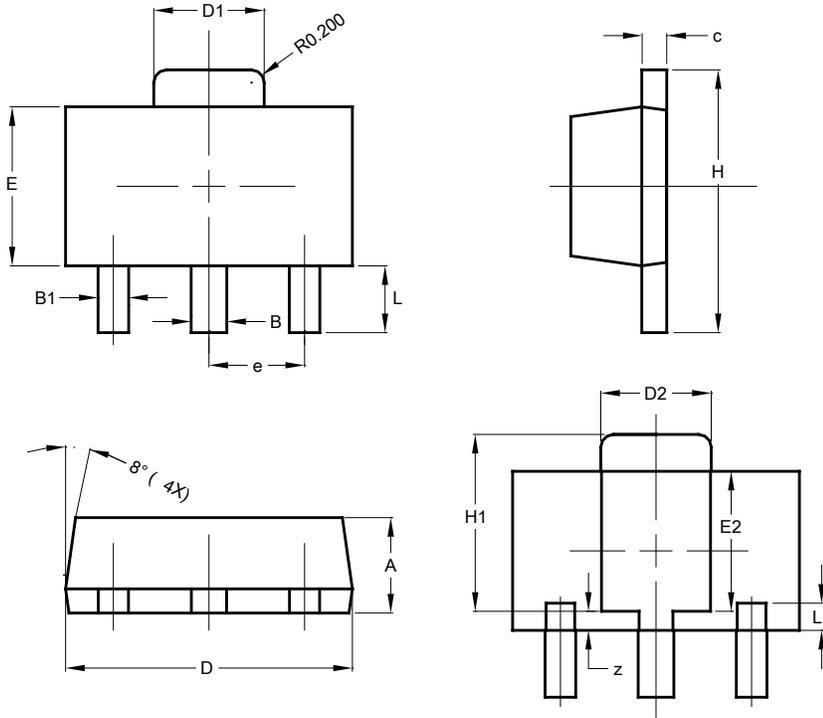
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	400	550	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CES}	400	550	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	400	450	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.1	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	<1	100	nA	$V_{CB} = 320\text{V}$
Collector Cutoff Current	I_{CES}	—	<1	100	nA	$V_{CES} = 320\text{V}$
Emitter Cutoff Current	I_{EBO}	—	<1	20	nA	$V_{EB} = 6\text{V}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{CE(sat)}$	—	—	200 500	mV	$I_C = 20\text{mA}, I_B = 2\text{mA}$ $I_C = 50\text{mA}, I_B = 6\text{mA}$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	—	—	900	mV	$I_C = 50\text{mA}, I_B = 5\text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	—	—	900	mV	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$
DC Current Gain (Note 11)	h_{FE}	100 100 15	—	300	—	$I_C = 1\text{mA}, V_{CE} = 10\text{V}$ $I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $I_C = 100\text{mA}, V_{CE} = 10\text{V}$
Transitional Frequency	f_T	50	—	—	MHz	$I_C = 10\text{mA}, V_{CE} = 20\text{V},$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}	—	—	5	pF	$V_{CB} = 20\text{V}, f = 1\text{MHz}$
Turn-On Time	t_{on}	—	135	—	ns	$I_C = 50\text{mA}, V_{CE} = 100\text{V},$
Turn-Off Time	t_{off}	—	2260	—	ns	$I_{B1} = 5\text{mA}, I_{B2} = -10\text{mA}$

 Note: 11. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

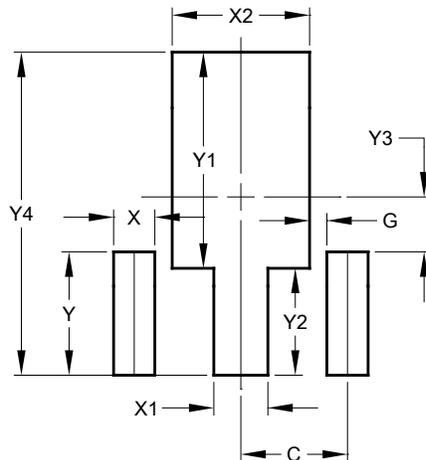


Package Outline Dimensions



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.